

ABSTRACT OF THE DISCLOSURE

The present invention provides the structure and manufacturing method of a semiconductor device that consumes small power even when a screen is made to be larger. A signal wiring line or a part of a gate wiring line is formed from a low
5 resistant material (typically aluminum) and p-channel TFTs are used for a pixel TFT of a pixel portion. The p-channel TFT in the pixel portion has a multi-gate structure in which a plurality of channel formation regions are provided in order to reduce fluctuation in OFF current.